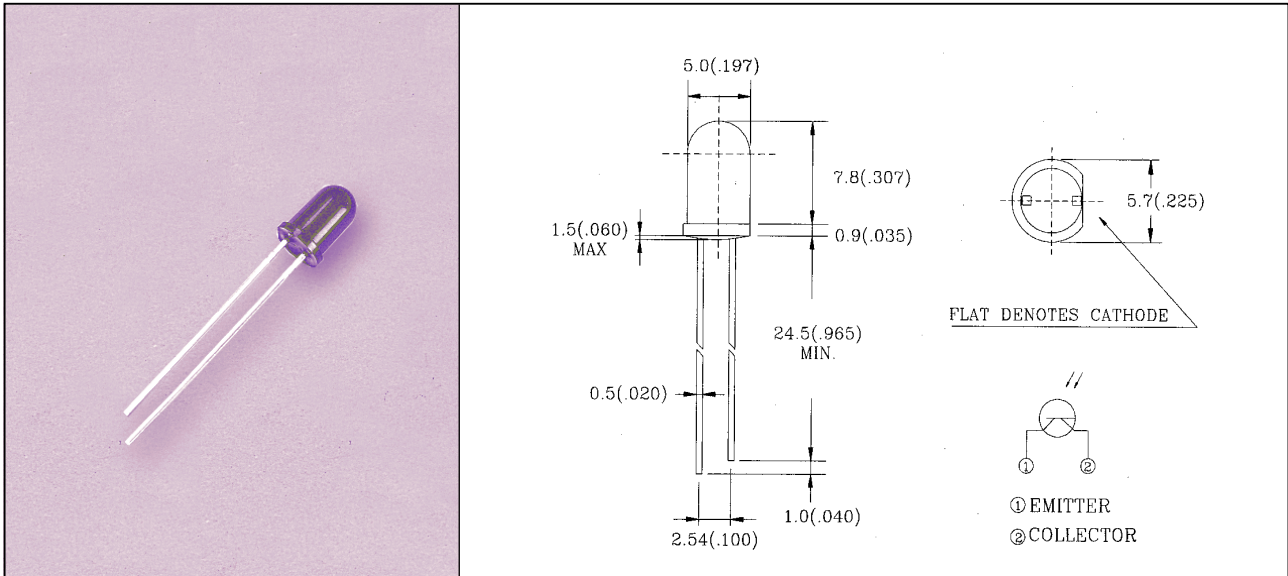


L-51ROPT1XX 5.0mm PHOTOTRANSISTOR



◆ **ABSOLUTE MAXIMUM RATING:(Ta=25°C)**

Part No.	P _D (mw)	V _{(BR)R} (V)	Topr	Tstg
L-51ROPT1XX	10	5	-35°C to 85°C	-35°C to 85°C
PARAMETER	Power Dissipation	Reverse break down voltage	Operating Temperature Range	Storage Temperature Range
Lead Soldering Temperature {1.6mm(0.063 inch)From Body}250°C ± 5°C For 3 Seconds				

◆ **ELECTRO-OPTICAL CHARACTERISTICS:(Ta=25°C)**

Part No.	BV _{CEO} (V)			BV _{ECO} (V)			I _{CEO} (nA)			V _{CE(s)} (V)			t _r /t _f (uS)			I _c (mA)			C _{CB} (pF)			λ (nm)		
	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	PEAK	MAX
L-51ROPT1C	30			5					100			0.4	15	15		1.8	2.4			6.4		400		1050
L-51ROPT1D1	30			5					100			0.4	15	15		1.7	2.2			6.4		900	940	
L-51ROPT1D2	30			5					100			0.4	15	15		1.7	2.2			6.4		800	870	
TEST CONDITION	I _C =100uA E _e =0mW/cm ²			I _E =100uA E _e =0mW/cm ²			V _E =20V E _e =0mW/cm ²			I _C =2mA E _e =0.5mW/cm ²			V _{CE} =5V I _C =1mA R _L =1000Ω			V _{CE} =5V E _e =0.1mW/cm ²			f=1MHZ V _{CB} =3V E _e =0mW/cm ²					
PARAMETER	COLLECTOR-EMITTER BREAKDOWN VOLTAGE			EMITTER-COLLECTOR BREAKDOWN VOLTAGE			COLLECTOR DARK CURRENT			COLLECTOR-EMITTER SATURATION VOLTAGE			RISE/FALL TIME			ON STATE COLLECTOR CURRENT			COLLECTOR -BASE CAPACITANCE			SPECTRAL SENSITIVITY WAVELENGTH		

D1,D2=BLACK

1.All dimension are in millimeters (inches).

2.Tolerance is ± 0.25 mm (0.01") unless otherwise specified.